

FDP65N06

N-Channel UniFET™ MOSFET

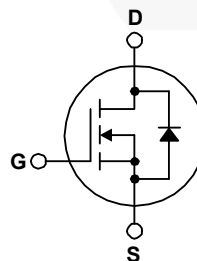
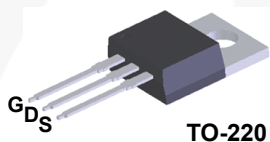
60 V, 65 A, 16 mΩ

Features

- $R_{DS(on)} = 13 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 32.5 \text{ A}$
- Low Gate Charge (typical 33 nC)
- Low C_{rss} (typical 35 pF)
- Fast Switching
- Improved dv/dt Capability

Description

UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol | Parameter | FDP65N06 | Units |
|----------------|--|-------------|---------------------|
| V_{DSS} | Drain-Source Voltage | 60 | V |
| I_D | Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$) | 65 | A |
| | | 41 | A |
| I_{DM} | Drain Current - Pulsed (Note 1) | 260 | A |
| V_{GSS} | Gate-Source Voltage | ± 20 | V |
| E_{AS} | Single Pulsed Avalanche Energy (Note 2) | 430 | mJ |
| I_{AR} | Avalanche Current (Note 1) | 65 | A |
| E_{AR} | Repetitive Avalanche Energy (Note 1) | 13.5 | mJ |
| dv/dt | Peak Diode Recovery dv/dt (Note 3) | 4.5 | V/ns |
| P_D | Power Dissipation ($T_C = 25^\circ\text{C}$) | 135 | W |
| | - Derate above 25°C | 1.08 | W/ $^\circ\text{C}$ |
| T_J, T_{STG} | Operating and Storage Temperature Range | -55 to +150 | $^\circ\text{C}$ |
| T_L | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds | 300 | $^\circ\text{C}$ |

Thermal Characteristics

| Symbol | Parameter | FDP65N06 | Units |
|-----------------|---|----------|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case, Max. | 0.92 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient, Max. | 62.5 | $^\circ\text{C}/\text{W}$ |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|----------|---------|-----------|------------|----------|
| FDP65N06 | FDP65N06 | TO-220 | Tube | N/A | 50 units |

Electrical Characteristics T_C = 25°C unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units | |
|---|---|--|----------|-------|-------|-------|----|
| Off Characteristics | | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0 V, I _D = 250 μA | 60 | - | - | V | |
| ΔBV _{DSS} / ΔT _J | Breakdown Voltage Temperature Coefficient | I _D = 250 μA, Referenced to 25°C | - | 0.5 | - | V/°C | |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 60 V, V _{GS} = 0 V | - | - | 1 | μA | |
| | | V _{DS} = 48 V, T _C = 125°C | - | - | 10 | μA | |
| I _{GSSF} | Gate-Body Leakage Current, Forward | V _{GS} = 20 V, V _{DS} = 0 V | - | - | 100 | nA | |
| I _{GSSR} | Gate-Body Leakage Current, Reverse | V _{GS} = -20 V, V _{DS} = 0 V | - | - | -100 | nA | |
| On Characteristics | | | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} , I _D = 250 μA | 2.0 | - | 4.0 | V | |
| R _{DS(on)} | Static Drain-Source On-Resistance | V _{GS} = 10 V, I _D = 32.5 A | - | 0.013 | 0.016 | Ω | |
| g _{FS} | Forward Transconductance | V _{DS} = 40 V, I _D = 32.5 A | - | 39 | - | S | |
| Dynamic Characteristics | | | | | | | |
| C _{iss} | Input Capacitance | V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz | - | 1670 | 2170 | pF | |
| C _{oss} | Output Capacitance | | - | 464 | 600 | pF | |
| C _{rss} | Reverse Transfer Capacitance | | - | 35 | 52 | pF | |
| Switching Characteristics | | | | | | | |
| t _{d(on)} | Turn-On Delay Time | V _{DD} = 30 V, I _D = 65A, R _G = 25 Ω | - | 24 | 58 | ns | |
| t _r | Turn-On Rise Time | | - | 94 | 200 | ns | |
| t _{d(off)} | Turn-Off Delay Time | | (Note 4) | - | 98 | 210 | ns |
| t _f | Turn-Off Fall Time | | (Note 4) | - | 52 | 114 | ns |
| Q _g | Total Gate Charge | V _{DS} = 48 V, I _D = 65A, V _{GS} = 10 V | - | 33 | 43 | nC | |
| Q _{gs} | Gate-Source Charge | | (Note 4) | - | 10 | - | nC |
| Q _{gd} | Gate-Drain Charge | | (Note 4) | - | 11 | - | nC |
| Drain-Source Diode Characteristics and Maximum Ratings | | | | | | | |
| I _S | Maximum Continuous Drain-Source Diode Forward Current | | - | - | 65 | A | |
| I _{SM} | Maximum Pulsed Drain-Source Diode Forward Current | | - | - | 260 | A | |
| V _{SD} | Drain-Source Diode Forward Voltage | V _{GS} = 0 V, I _S = 65 A | - | - | 1.4 | V | |
| t _{rr} | Reverse Recovery Time | V _{GS} = 0 V, I _S = 65 A, di _F / dt = 100 A/μs | - | 62 | - | ns | |
| Q _{rr} | Reverse Recovery Charge | | - | 132 | - | nC | |

NOTES:

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. L = 47 μH, I_{AS} = 65 A, V_{DD} = 50 V, R_G = 25 Ω, Starting T_J = 25°C.
3. I_{SD} ≤ 65 A, di/dt ≤ 200 A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C.
4. Essentially independent of operating temperature.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

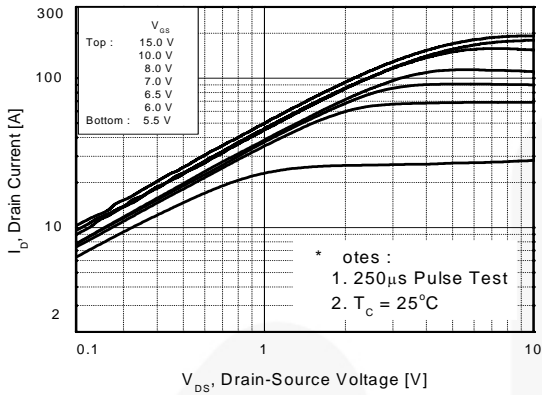


Figure 2. Transfer Characteristics

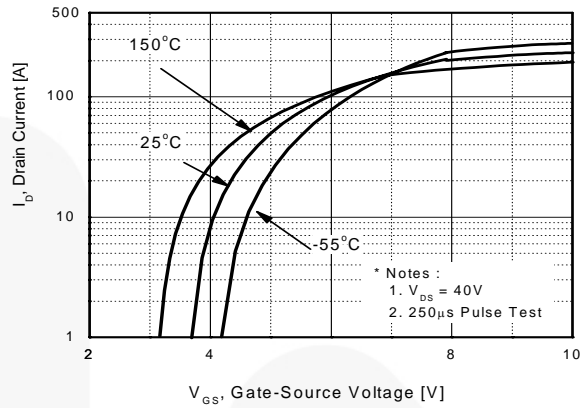


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

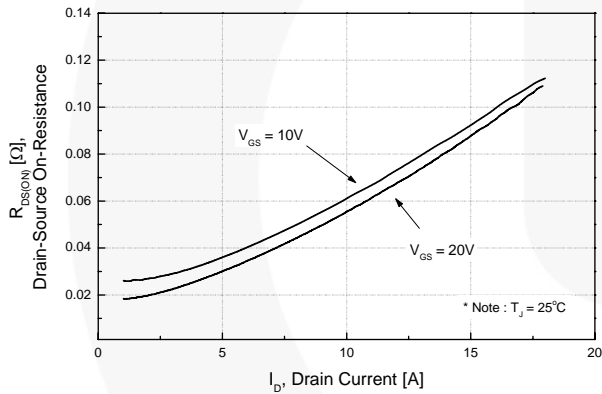


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

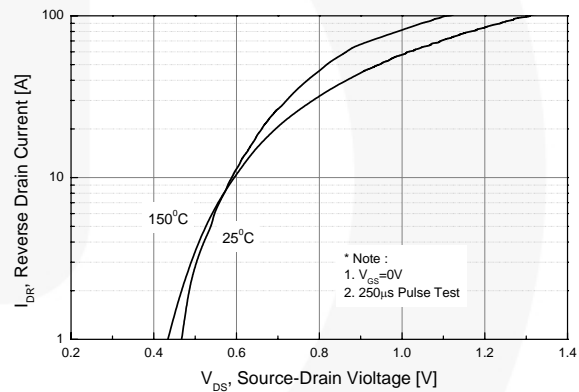


Figure 5. Capacitance Characteristics

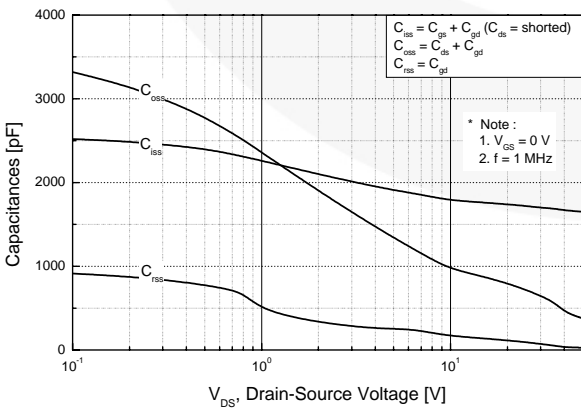
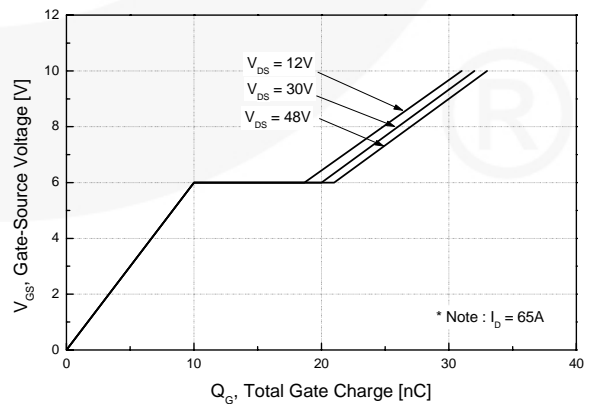


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

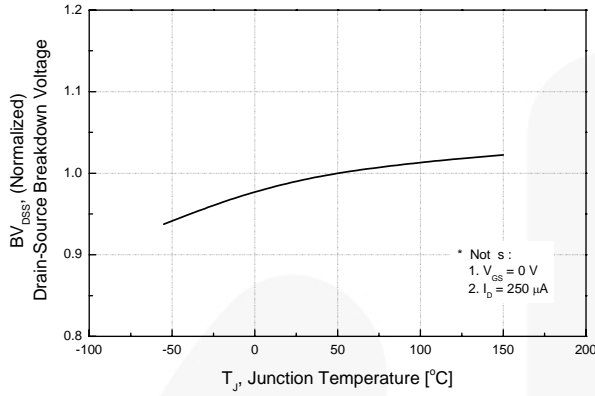


Figure 8. On-Resistance Variation vs. Temperature

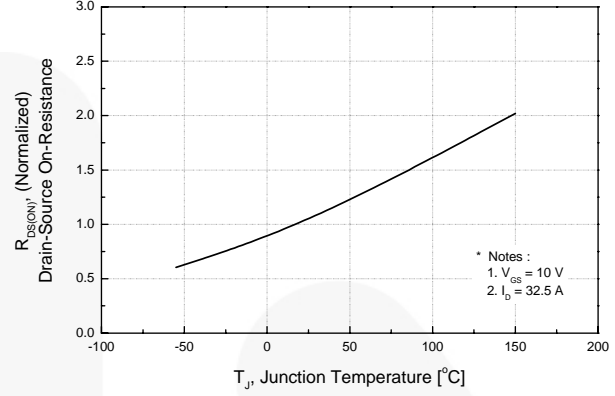


Figure 9. Maximum Safe Operating Area

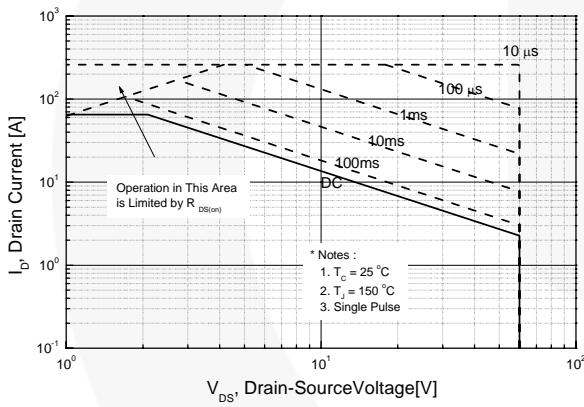


Figure 10. Maximum Drain Current vs. Case Temperature

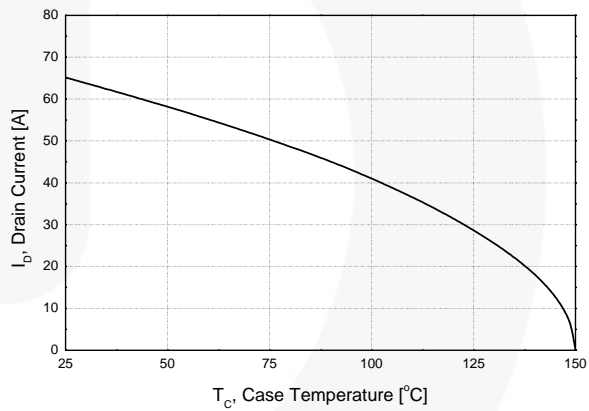


Figure 11. Transient Thermal Response Curve

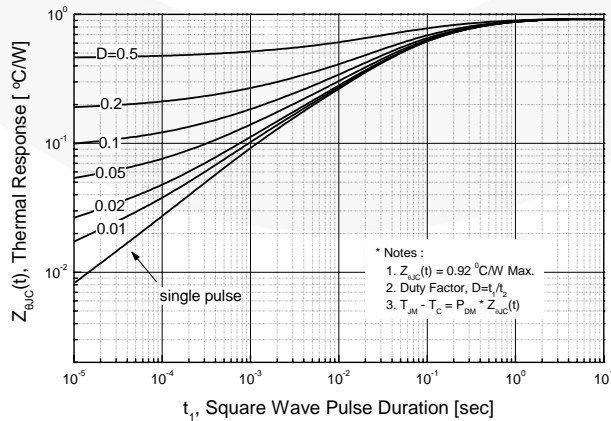


Figure 12. Gate Charge Test Circuit & Waveform

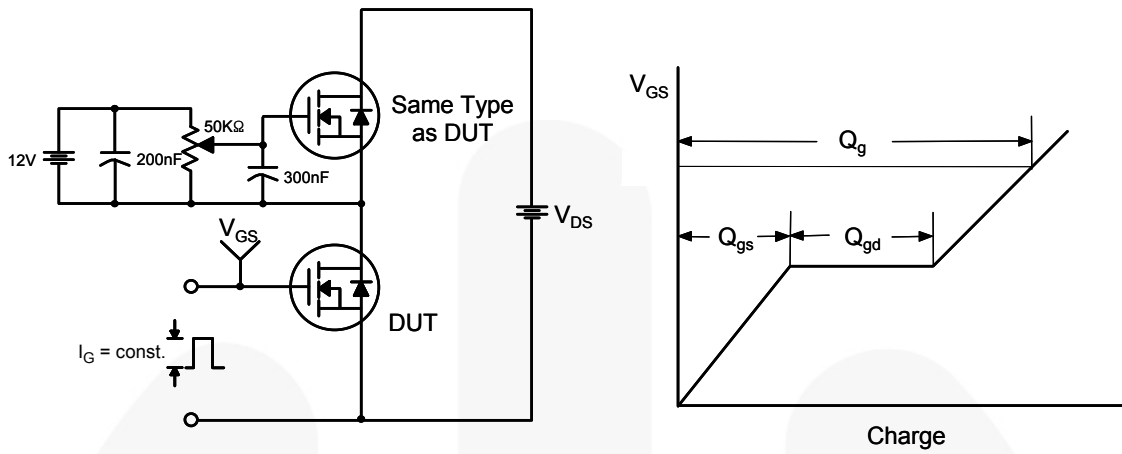


Figure 13. Resistive Switching Test Circuit & Waveforms

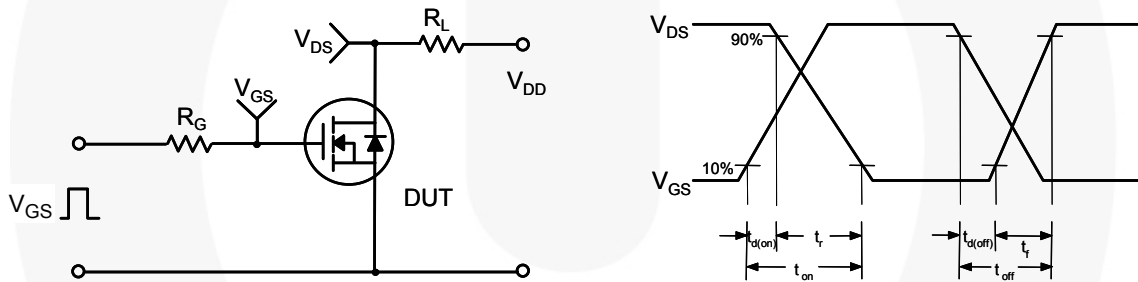


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

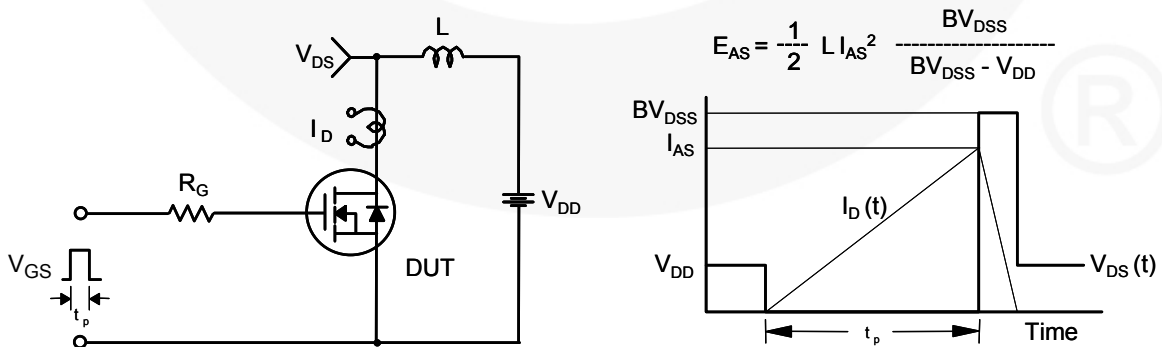
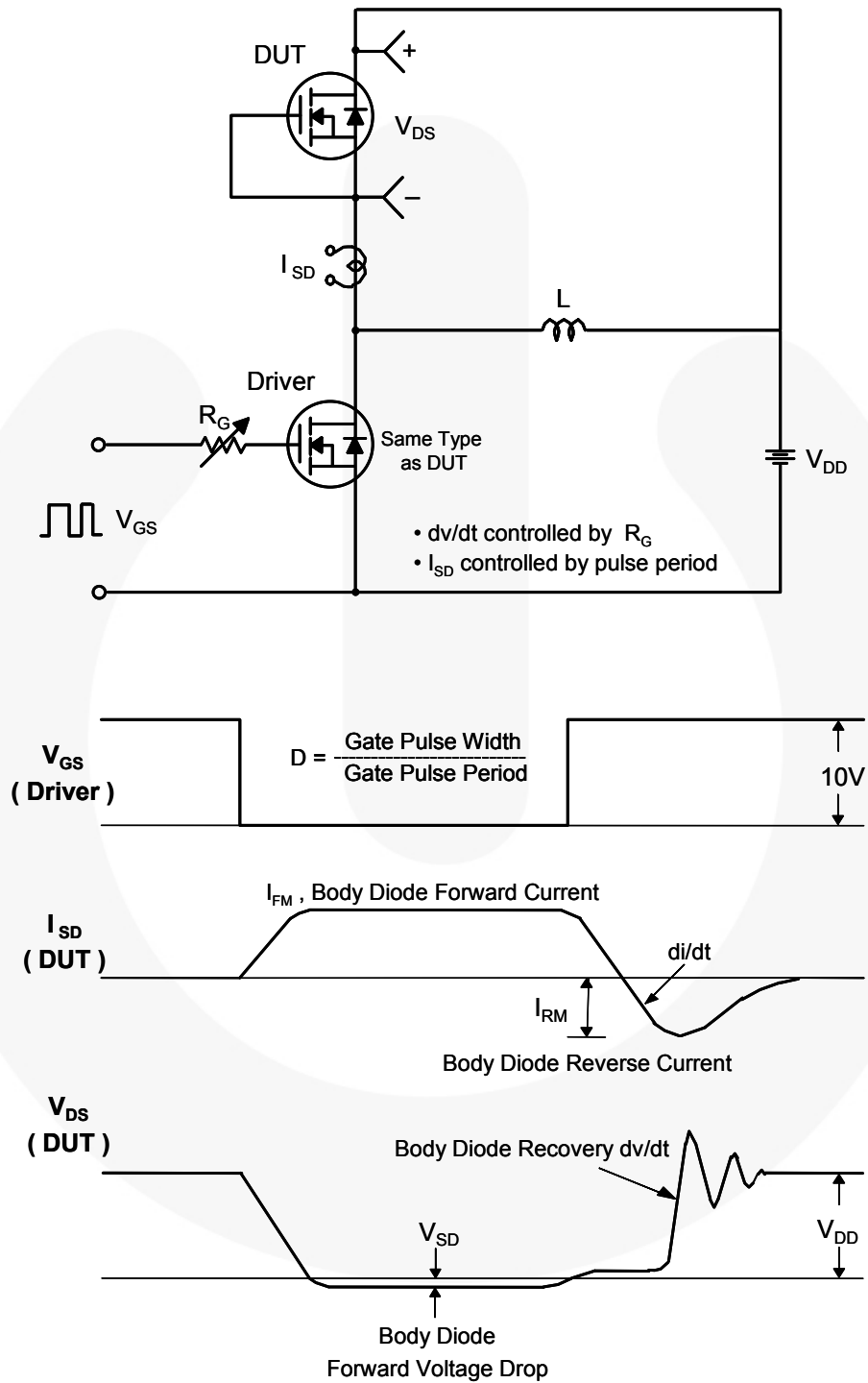


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

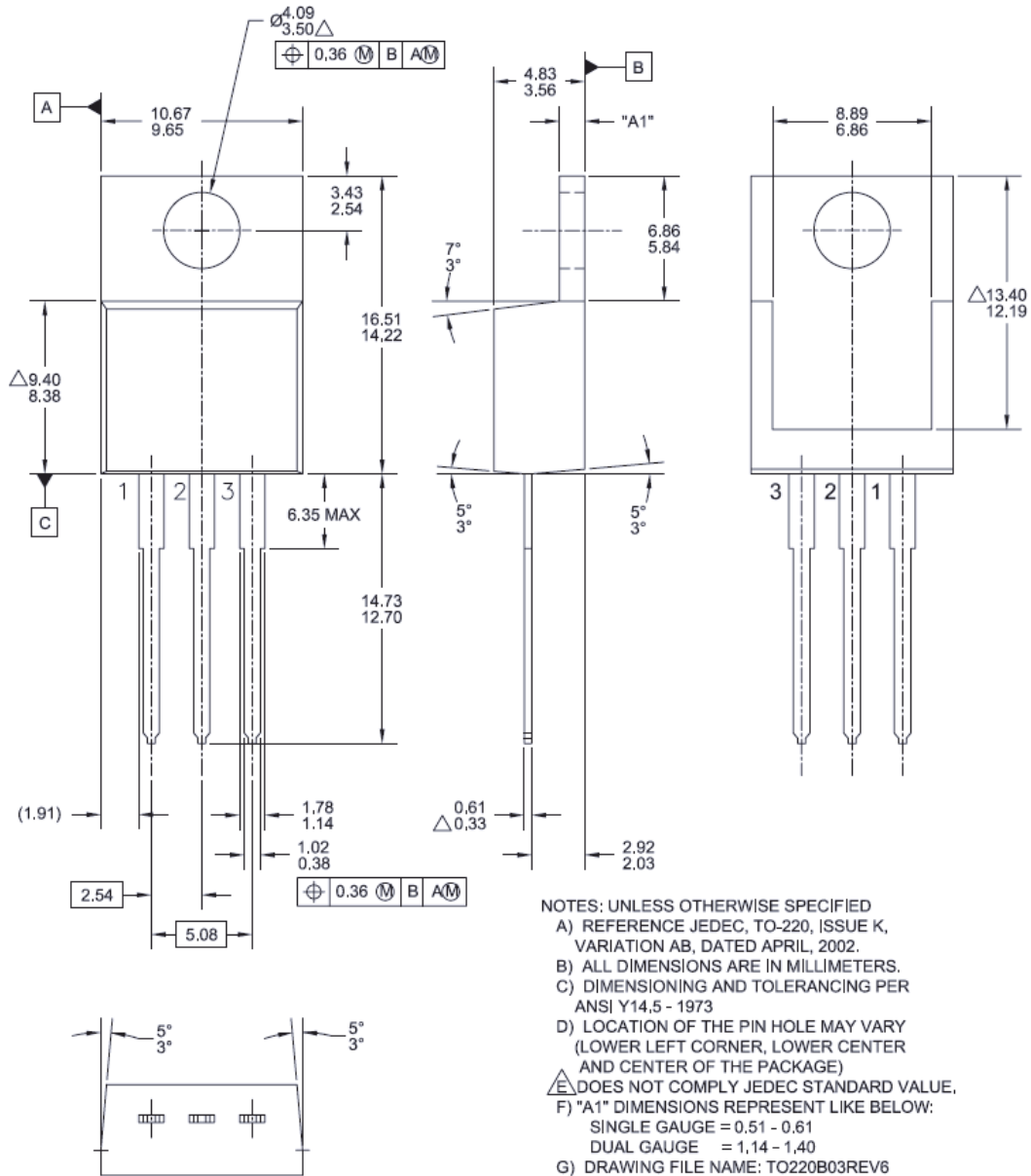


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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